

Amendments to the Claims

This listing of the Claims will replace all prior versions and listings of the claims in this patent application.

Listing of the Claims

Claims 1-93 (canceled)

94. (currently amended) ~~An electronic component~~ A semiconductor chip or wafer comprising:

a silicon ~~semiconductor~~-substrate ~~having multiple semiconductor devices~~;

a first ~~an interconnecting~~-metallization structure over said silicon ~~semiconductor~~ substrate;

a passivation ~~an insulating~~-layer over said ~~interconnecting~~ first metallization structure; and

a second ~~an upper~~-metallization structure over said passivation ~~insulating~~-layer, wherein said second ~~upper~~-metallization structure comprises a metal layer having a thickness of between 2 and 100 μm , and wherein said second ~~upper~~-metallization structure connects multiple separate portions of said first ~~interconnecting~~-metallization structure.

95. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 94, wherein said passivation ~~insulating~~ layer comprises a topmost nitride layer of said semiconductor chip or wafer.

96. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 94, wherein said ~~insulating layer comprises a~~ passivation layer comprises a topmost oxide layer of said semiconductor chip or wafer.

97. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 94, wherein said passivation ~~insulating~~ layer comprises a topmost CVD-formed layer of said semiconductor chip or wafer.

98. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 94, wherein said ~~interconnecting~~ first metallization structure comprises a first contact pad exposed by an opening in said passivation ~~insulating~~ layer, and said second ~~upper~~ metallization structure comprises a second contact pad connected to said first contact pad, wherein the positions of said first and second contact pads from a top view are different.

99. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 94, wherein said metal layer comprises gold.

100. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 99, wherein said second ~~upper~~ metallization structure further comprises an underlying metal

layer under said metal layer, wherein said underlying metal layer comprises titanium tungsten.

Claim 101 (canceled)

102. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 94 further comprising a topmost polymer layer over said ~~insulating passivation~~ layer, wherein said second upper metallization structure is over said topmost polymer layer.

Claims 103 and 104 (canceled)

105. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 94, wherein said metal layer is electroplated.

106. (currently amended) A semiconductor chip or wafer ~~An electronic component~~ comprising:

a silicon ~~semiconductor~~ substrate having multiple semiconductor devices;

a first ~~an interconnecting~~ metallization structure over said ~~semiconductor silicon~~ substrate, wherein said first metallization structure ~~and comprising comprises~~ a first contact pad;

a passivation ~~an insulating~~ layer over said ~~interconnecting first~~ metallization structure, wherein an opening in said passivation layer exposes said first contact pad ~~is exposed by an opening in said insulating layer~~; and

a second ~~an upper~~ metallization structure over said passivation ~~insulating~~ layer, wherein said second metallization structure ~~and comprising~~ comprises a gold layer with a thickness of between 2 and 100 μm , wherein said ~~upper~~ second metallization structure comprises a second contact pad connected to said first contact pad, and wherein the positions of said first and second contact pads from a top view are different.

107. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 106, wherein said passivation ~~insulating~~ layer comprises a topmost nitride layer of said semiconductor chip or wafer.

108. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 106, wherein said ~~insulating layer~~ comprises a passivation layer comprises a topmost oxide layer of said semiconductor chip or wafer.

109. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 106, wherein said passivation ~~insulating~~ layer comprises a topmost CVD-formed layer of said semiconductor chip or wafer.

110. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 106, wherein said second ~~upper~~ metallization structure further comprises a metal layer under said gold layer, wherein said metal layer comprises titanium tungsten.

Claim 111 (canceled)

112. (currently added) The semiconductor chip or wafer ~~electronic component~~ of claim 106, wherein said second contact pad is used to be wirebonded thereto.

113. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 106 further comprising a wirebond on ~~connected to~~ said second contact pad.

114. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 106 further comprising a metal bump on said second contact pad.

115. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 106 further comprising a solder bump on said second contact pad..

116. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 106 further comprising a topmost polymer layer over said passivation ~~insulating~~ layer, wherein said gold layer is upper metallization structure ~~comprises an upper metal layer over~~ said topmost polymer layer.

Claims 117 and 118 (canceled)

119. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 106, wherein said gold layer is electroplated.

120. (currently amended) A semiconductor chip or wafer ~~An electronic component~~
comprising:

- a silicon ~~semiconductor~~ substrate ~~having multiple semiconductor devices~~;
- a first ~~an interconnecting~~ metallization structure over said silicon ~~semiconductor~~ substrate, wherein said first metallization structure comprises a first contact pad; ~~and comprising a contact point~~;
- a passivation layer over said first ~~interconnecting~~ metallization structure, wherein an opening in said passivation layer exposes said first contact pad; ~~and point is exposed by an opening in said passivation layer;~~ and
- a second contact pad connected to said first contact pad, ~~point~~, wherein said second contact pad comprises a gold layer with a thickness of between 2 and 100 μm and is used to be wirebonded thereto.

Claims 121 and 122 (canceled)

123. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 120 further comprising a polymer layer over said passivation layer, wherein said second contact pad is over said polymer layer.

Claims 124 and 125 (canceled)

126. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 120, wherein said passivation ~~insulating~~ layer comprises a topmost nitride layer of said semiconductor chip or wafer.

127. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 120, wherein said passivation ~~insulating~~ layer comprises a topmost oxide layer of said semiconductor chip or wafer.

128. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 120, wherein said passivation layer comprises a topmost CVD-formed layer of said semiconductor chip or wafer.

129. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 120, wherein said gold layer is electroplated.

Claim 130 (canceled)

131. (currently amended) The semiconductor chip or wafer ~~electronic component~~ of claim 120 further comprising a wirebond on ~~connected to~~ said second contact pad.

Claims 132-135 (canceled)